Ordering number:EN2853

NPN Triple Diffused Planar Silicon Transistor

2SC4430

800V/12A Switching Regulator Applications

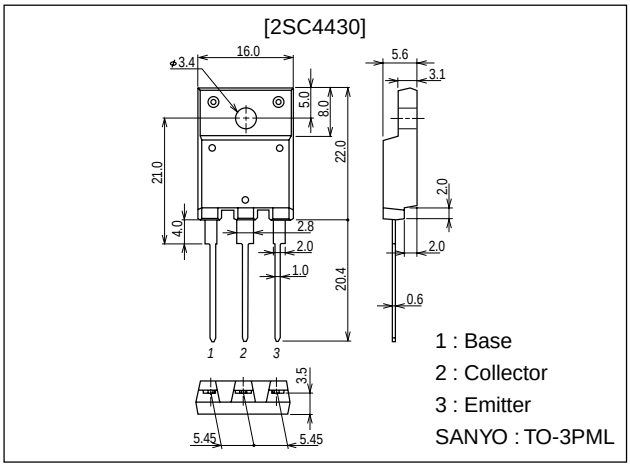
Features

- High breakdown voltage, high reliability.
- Fast switching speed (t_f : 0.1μs typ).
- Wide ASO.
- Adoption of MBIT process.
- Micaless package facilitating easy mounting.

Package Dimensions

unit:mm

2039D



Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		1100	V
Collector-to-Emitter Voltage	V_{CEO}		800	V
Emitter-to-Base Voltage	V_{EBO}		7	V
Collector Current	I_C		12	A
Collector Current (Pulse)	I_{CP}	PW≤300μs, duty cycle≤10%	30	A
Base Current	I_B		6	A
Collector Dissipation	P_C		3	W
		Tc=25˚C	65	W
Junction Temperature	Tj		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=800V, I_E=0			10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=5V, I_C=0			10	μA
DC Current Gain	$h_{FE}1$*	V_{CE}=5V, I_C=0.8A	10		40	
	$h_{FE}2$	V_{CE}=5V, I_C=4A	8			

* : The $h_{FE}1$ of the 2SC4430 is classified as follows. When specifying the $h_{FE}1$ rank, specify two ranks or more in principle.

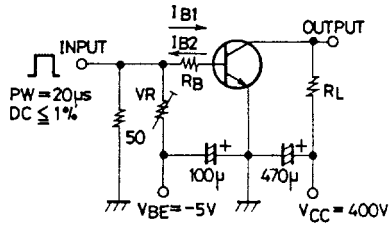
10 K 20	15 L 30	20 M 40

SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters

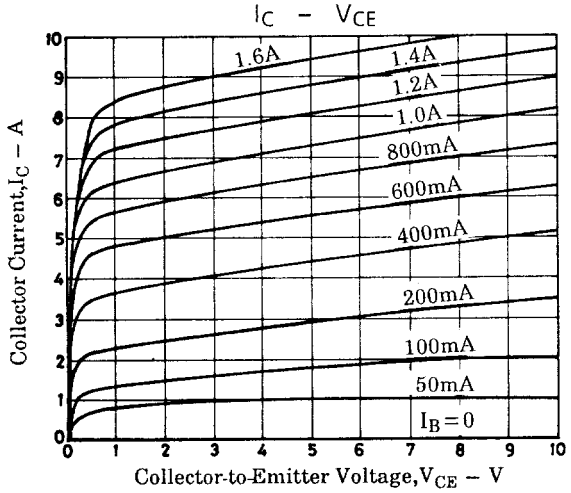
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

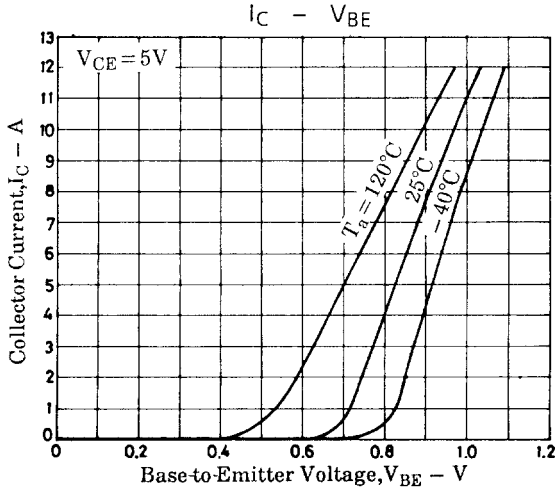
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=6A, I_B=1.2A			2.0	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=6A, I_B=1.2A			1.5	V
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=0.8A		15		MHz
Output Capacitance	C_{ob}	V_{CB}=10V, f=1MHz		215		pF
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=1mA, I_E=0	1100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=5mA, R_{BE}=∞	800			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	7			V
Collector-to-Emitter Sustain Voltage	$V_{CEX(sus)}$	I_C=6A, I_{B1}=1.2A, I_{B2}=–1.2A, L=500μH, Clamped	800			V
Turn-ON Time	t_{on}	I_C=8A, I_{B1}=1.6A, I_{B2}=–3.2A, R_L=50Ω, V_{CC}=400V			0.5	μs
Storage Time	t_{stg}	I_C=8A, I_{B1}=1.6A, I_{B2}=–3.2A, R_L=50Ω, V_{CC}=400V			3.0	μs
Fall Time	t_f	I_C=8A, I_{B1}=1.6A, I_{B2}=–3.2A, R_L=50Ω, V_{CC}=400V			0.3	μs

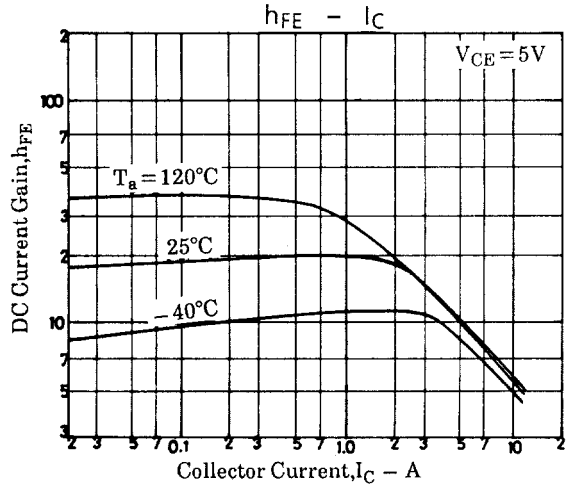
Switching Time Test Circuit

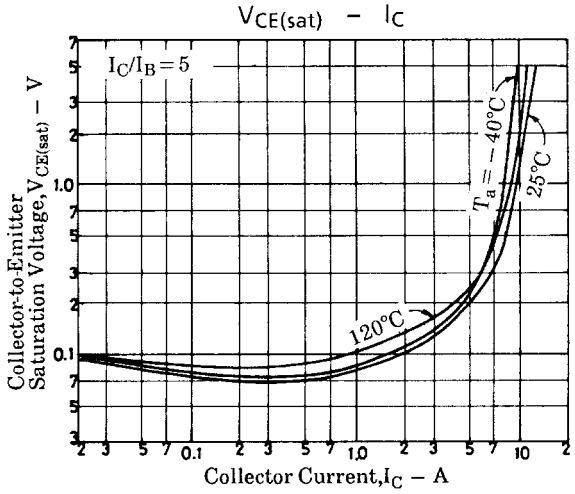


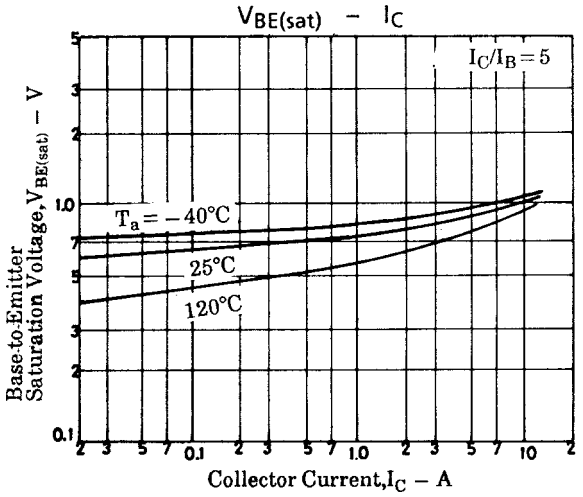
Unit (resistance : Ω, capacitance : F)

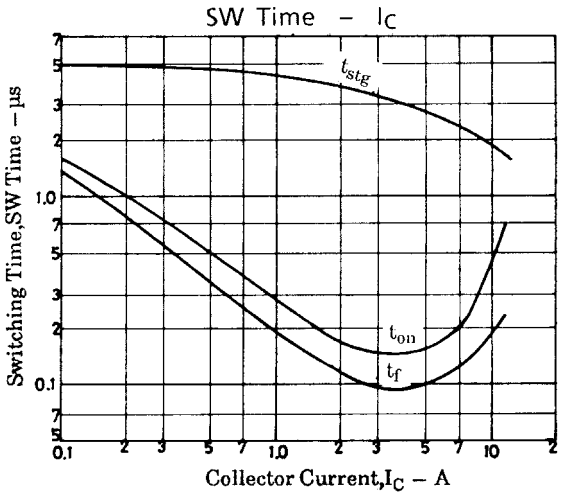


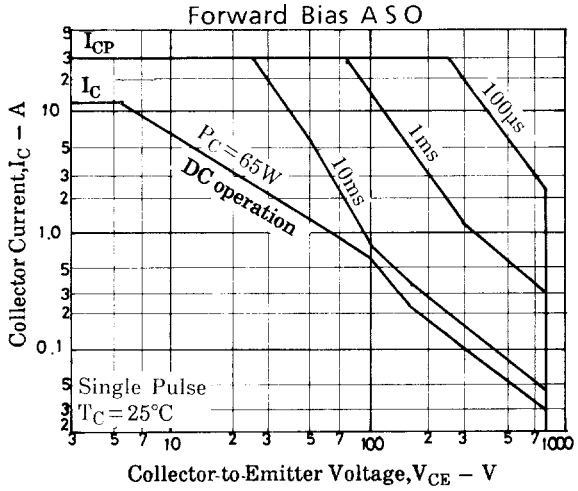


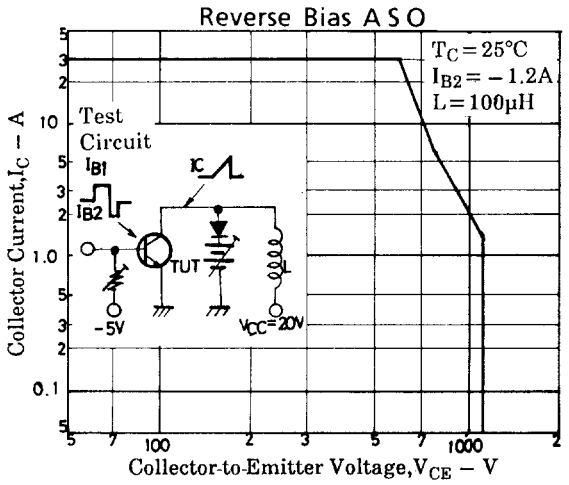


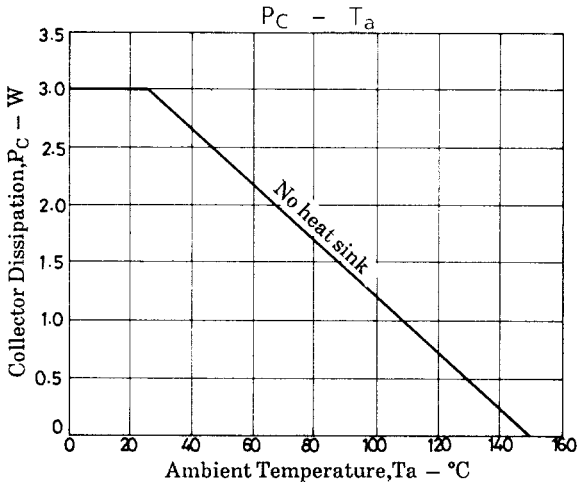


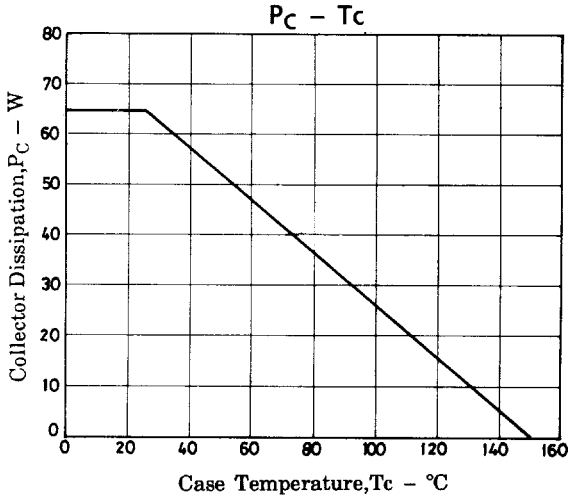

VBE(sat) – IC
IC/IB = 5
Ta = –40°C
25°C
120°C
Base-to-Emitter Saturation Voltage, VBE(sat) – V
Collector Current, IC – A

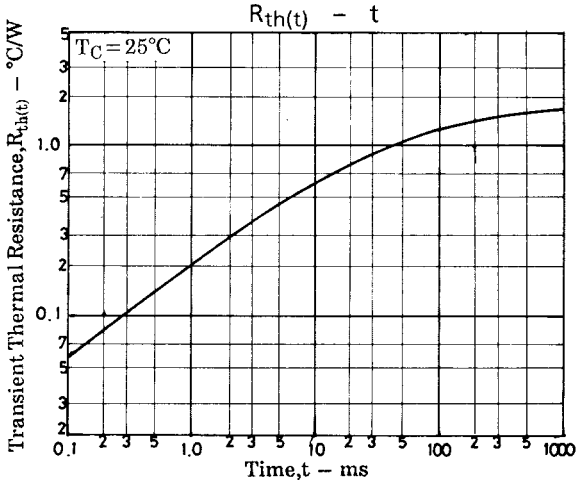

SW Time – IC
tstg
ton
tf
Switching Time, SW Time – µs
Collector Current, IC – A


Forward Bias A S O
ICP
IC
PC = 65W
DC operation
100µs
1ms
10ms
Single Pulse
TC = 25°C
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V


Reverse Bias A S O
TC = 25°C
IB2 = – 1.2A
L = 100µH
Test Circuit
IB1
IB2
IC
TUT
L
–5V
VCC = 20V
Collector Current, IC – A
Collector-to-Emitter Voltage, VCE – V


PC – Ta
No heat sink
Collector Dissipation, PC – W
Ambient Temperature, Ta – °C


PC – Tc
Collector Dissipation, PC – W
Case Temperature, Tc – °C


Rth(t) – t
TC = 25°C
Transient Thermal Resistance, Rth(t) – °C/W
Time, t – ms